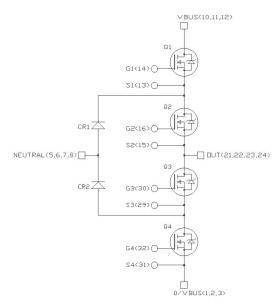
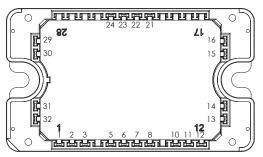
MSCSM70TLM44C3AG

Three Level Inverter SiC MOSFET Power Module

Product Overview

The MSCSM70TLM44C3AG device is a 700V/58A three level inverter silicon carbide (SiC) MOSFET power module.





Notes:

- All ratings at T_J = 25 °C, unless otherwise specified.
- 2. All multiple inputs and outputs must be shorted together: 1/2/3; 10/11/12; 5/6/7/8; 21/22/23/24

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

Features

The following are the key features of the MSCSM70TLM44C3AG device:

- SiC Power MOSFET
 - Low R_{DS(on)}
 - High temperature performance
- · SiC Schottky Diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature Independent switching behavior
 - Positive temperature coefficient on VF
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Aluminum Nitride (AIN) substrate for improved thermal performance

Benefits

The following are the benefits of the MSCSM70TLM44C3AG device:

- High efficiency converter
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Low profile
- **RoHS Compliant**

Applications

The following are the applications of the MSCSM70TLM44C3AG device:

· Uninterruptible power supplies

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1. **Electrical Specifications**

This section provides the electrical specifications of the MSCSM70TLM44C3AG device.

SiC MOSFET Characteristics (Per SiC MOSFET) 1.1

The following table lists the absolute maximum ratings of the MSCSM70TLM44C3AG device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter	Parameter		Unit
V _{DSS}	Drain-Source voltage	Drain-Source voltage		V
I _D	Continuous drain current	Continuous drain current T _C = 25 °C		Α
	T _C = 80 °C		46	
I _{DM}	Pulsed drain current	Pulsed drain current		
V _{GS}	Gate-Source voltage	Gate-Source voltage		V
R _{DS(on)}	Drain-Source ON resistance	Drain-Source ON resistance		mΩ
P _D	Power dissipation	T _C = 25 °C	176	W

The following table lists the electrical characteristics of the MSCSM70TLM44C3AG device.

Table 1-2. Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0V V _{DS} = 700V		_	_	100	μΑ
R _{DS(on)}	Drain-Source on	V _{GS} = 20V	T _J = 25 °C	_	35	44	mΩ
	resistance	I _D = 30A	T _J = 175 °C	_	41	_	
V _{GS(th)}	Gate threshold voltage	$V_{GS} = V_{DS}$ $I_D = 2 \text{ mA}$		1.9	2.7	_	V
I _{GSS}	Gate-Source leakage current	$V_{GS} = 20V$ $V_{DS} = 0V$		_	_	150	nA

The following table lists the dynamic characteristics of the MSCSM70TLM44C3AG device.

Table 1-3. Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
C _{iss}	Input capacitance	V _{GS} = 0V		_	2010	_	pF
C _{oss}	Output capacitance	V _{DS} = 700V		_	247	_	
C _{rss}	Reverse transfer capacitance	f = 1 MHz		_	17	_	
Qg	Total gate charge	$V_{GS} = -5V/20V$		_	99	_	nC
Q _{gs}	Gate-source charge	V _{Bus} = 470V		_	33	_	
Q _{gd}	Gate-drain charge	I _D = 30A		_	18	_	
T _{d(on)}	Turn-on delay time	V _{GS} = -5V/20V		_	40	_	ns
T _r	Rise time	$V_{Bus} = 400V$ $I_D = 40A$		_	35	_	
T _{d(off)}	Turn-off delay time			_	50	_	
Tf	Fall time	T_J = 150 °C R_{GON} = 54 Ω R_{GOFF} = 9.4 Ω		20	_		
E _{on}	Turn-on energy	V _{GS} = -5V/20V	T _J = 150 °C	_	272	_	μJ
E _{off}	Turn-off energy	V_{Bus} = 400V I_{D} = 40A R_{GON} = 54 Ω R_{GOFF} = 9.4 Ω		_	93	_	μJ
R _{Gint}	Internal gate resistance			_	1.13	_	Ω
R _{thJC}	Junction-to-case therr	mal resistance		_	_	0.85	°C/W

The following table lists the body diode ratings and characteristics of the MSCSM70TLM44C3AG device.

Table 1-4. Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
V _{SD}	Diode forward voltage	V _{GS} = 0V	_	3.8	_	V
		I _{SD} = 30A				
		V _{GS} = -5V	_	4	_	
		I _{SD} = 30A				
t _{rr}	Reverse recovery time	I _{SD} = 30A	_	75	_	ns
Q _{rr}	Reverse recovery charge	$V_{GS} = -5V$	_	305	_	nC
I _{rr}	Reverse recovery current	V _R = 400V	_	11	_	Α
		di _F /dt = 1000 A/µs				

1.2 SiC Diode Ratings and Characteristics (Per SiC Diode)

The following table lists the SiC diode ratings and characteristics of the MSCSM70TLM44C3AG device.

Table 1-5. SiC Diode Ratings and Characteristics

Symbol	Characteristic	Test Condition	Test Conditions		Тур	Max	Unit
V_{RRM}	Peak repetitive reverse voltage	_		_	_	700	V
I _{RRM}	Reverse leakage current	V _R = 700V	T _J = 25 °C	_	15	200	μΑ
			T _J = 175 °C	_	250	_	
I _F	DC forward current	_	T _C = 80 °C	_	50	_	A
V _F	Diode forward voltage		T _J = 25 °C	_	1.5	1.8	V
			T _J = 175 °C	_	1.9	_	
Q _C	Total capacitive charge	V _R = 400V	V _R = 400V		133	_	nC
С	Total capacitance	$f = 1 \text{ MHz}$ $V_R = 200V$ $f = 1 \text{ MHz}$ $V_R = 400V$		_	248	_	pF
				_	216	_	
R _{thJC}	Junction-to-case thermal re	esistance		_	_	0.86	°C/W

1.3 Thermal and Package Characteristics

The following table lists the package characteristics of the MSCSM70TLM44C3AG device.

Table 1-6. Thermal and Package Characteristics

Symbol	Characteristic	Min	Max	Unit		
V _{ISOL}	RMS isolation voltage, any terminal to ca	4000	_	V		
T _J	Operating junction temperature range	-40	175	°C		
T _{JOP}	Recommended junction temperature und	-40	T _{Jmax} –25			
T _{STG}	Storage temperature range	-40	125			
T _C	Operating case temperature	-40	125			
Torque	Mounting torque	2	3	N.m		
Wt	Package weight			_	110	g

1.4 Typical SiC MOSFET Performance Curve

The following figures show the SiC MOSFET performance curves of the MSCSM70TLM44C3AG device.

Figure 1-1. Maximum Thermal Impedance

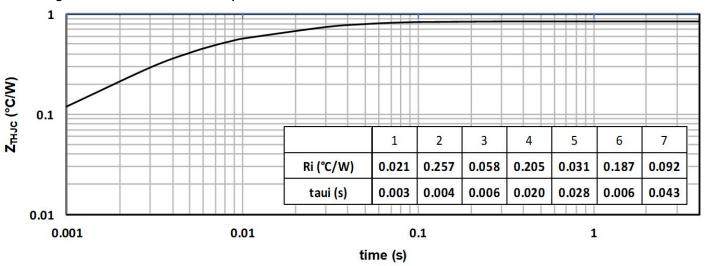


Figure 1-2. Output Characteristics, $T_J = 25$ °C

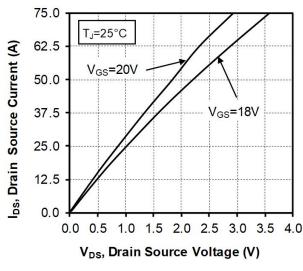


Figure 1-3. Output Characteristics, T_J = 175 °C

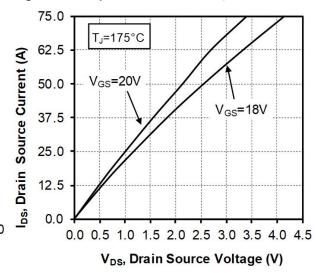


Figure 1-4. Normalized R_{DS(on)} vs. Temperature

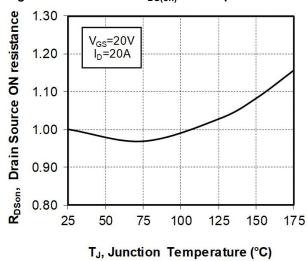


Figure 1-5. Transfer Characteristics

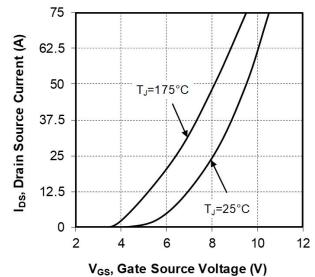


Figure 1-6. Turn On Energy vs Rg

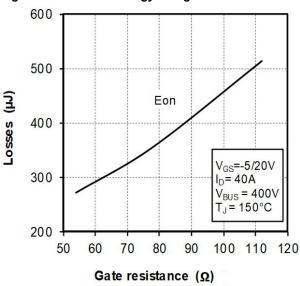


Figure 1-7. Switching Energy vs. Current

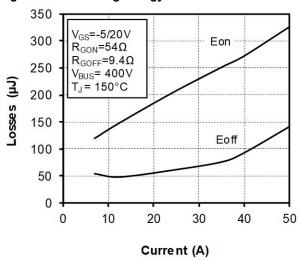
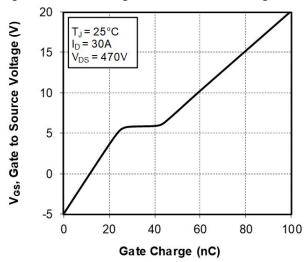


Figure 1-8. Capacitance vs. Drain Source Voltage

10000
Ciss
1000
Coss
100
Crss

Figure 1-9. Gate Charge vs. Gate Source Voltage



V_{DS}, Drain source Voltage (V)

400

600

Figure 1-10. Body Diode Characteristics, T_J = 25 °C

200

1

0

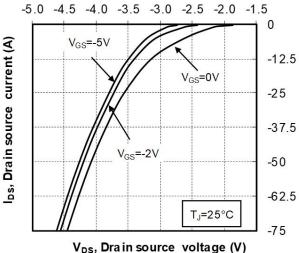


Figure 1-11. 3rd Quadrant Characteristics, T_J = 25 °C

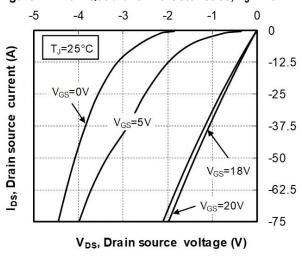
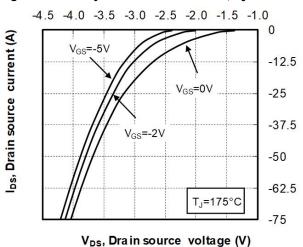
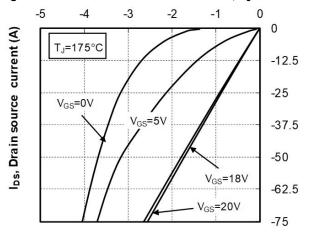


Figure 1-12. Body Diode Characteristics, T_{.J} = 175 °C Figure 1-13. 3rd Quadrant Characteristics, T_{.J} = 175 °C





V_{DS}, Drain source voltage (V)

Figure 1-14. Operating Frequency vs. Drain Current

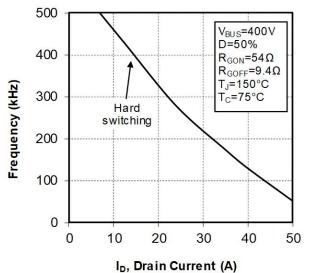
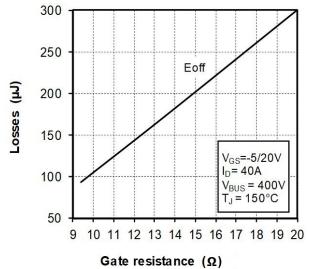


Figure 1-15. Turn Off Energy vs. Rg



1.5 Typical SiC Diode Performance Curve

The following figures show the SiC diode performance curves of the MSCSM70TLM44C3AG device.

Figure 1-16. Maximum Thermal Impedance

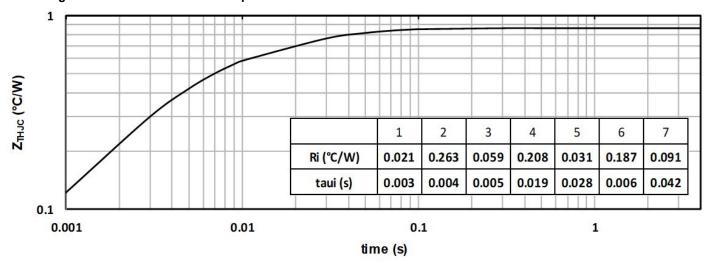


Figure 1-17. Forward Characteristics

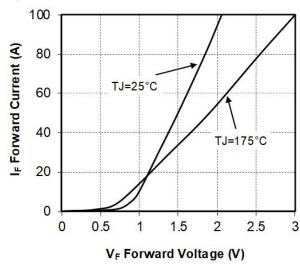
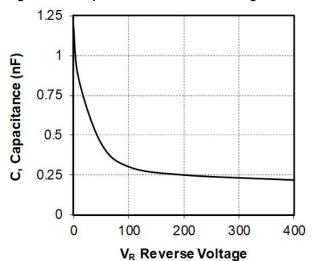


Figure 1-18. Capacitance vs. Reverse Voltage



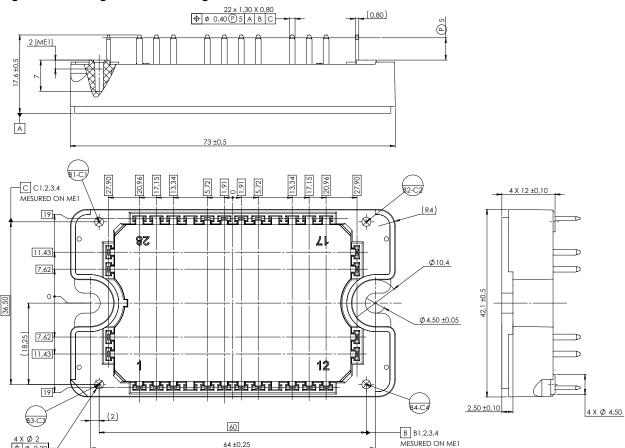
2. Package Specifications

The following section shows the package specification of the MSCSM70TLM44C3AG device.

2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM70TLM44C3AG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



Note: See application note AN3500A—Mounting Instructions for SP1F and SP3F Power Modules for more information.

MSCSM70TLM44C3AG

Revision History

3. Revision History

Revision	Date	Description
Α	01/2022	Initial Revision.

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